

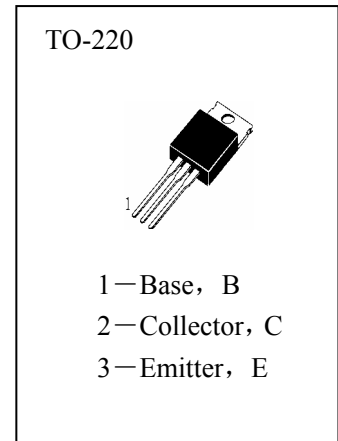


■ APPLICATIONS

High Breakdown Voltage And High Reliability. Fast Switching Speed.

■ ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

- T_{stg}—Storage Temperature..... -55~150°C
- T_j—Junction Temperature..... 150°C
- P_C—Collector Dissipation(T_c=25°C).....50W
- V_{CB0}—Collector-Base Voltage.....500V
- V_{CEO}—Collector-Emitter Voltage.....400V
- V_{EBO}—Emitter-Base Voltage.....7V
- I_C—Collector Current.....7A
- I_b—Base Current.....3A



■ ELECTRICAL CHARACTERISTICS (T_a=25°C)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV _{CB0}	Collector-Base Breakdown Voltage	500			V	I _C =1mA, I _E =0
BV _{CEO}	Collector-Emitter Breakdown Voltage	400			V	I _C =5mA, I _B =0
BV _{EBO}	Emitter-Base Breakdown Voltage	7			V	I _E =1mA, I _C =0
I _{CBO}	Collector Cut-off Current			10	μ A	V _{CB} =400V, I _E =0
I _{EBO}	Emitter Cut-off Current			10	μ A	V _{EB} =5V, I _C =0
H _{FE} (1)	DC Current Gain	15		50		V _{CE} =5V, I _C =0.8A
H _{FE} (2)	DC Current Gain	10				V _{CE} =5V, I _C =4A
H _{FE} (3)	DC Current Gain	10				V _{CE} =5V, I _C =10mA
V _{CE(sat)}	Collector- Emitter Saturation Voltage			0.8	V	I _C =4A, I _B =0.8A
V _{BE(sat)}	Base-Emitter Saturation Voltage			1.5	V	I _C =4A, I _B =0.8A
f _T	Current Gain-Bandwidth Product		20		MHz	V _{CE} =10V, I _C =0.8A
C _{ob}	Output Capacitance		80		pF	V _{CB} =10V, I _E =0, f=1MHz
t _{ON}	Turn-On Time			0.5	μ S	V _{CC} =10V, I _C =5A I _{B1} =1A, I _{B2} =-2A R _L =40ohms
t _{STG}	Storage Time			2.5	μ S	
t _F	Fall Time			0.3	μ S	

■ h_{FE} Classification

L	M	N
15—30	20—40	30—50